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Table of Contents

Monday, October 1, 2007

1. Wireless Transceivers and Building Blocks

Monday AM — *Ballroom 1*

Session Chair: D. Teeter

Co-Chair: F. Badets

(1.1) 9:50 – 10:15 AM – A Zero-Second-IF SiGe BiCMOS Satellite Radio Tuner Using a Single PLL for Both RF and IF LO Generation and a Replica Ring-VCO Calibrated IF Filter p.1

A. Maxim, M. Gheorge, and C. Turinici

(1.2) 10:15 – 10:40 AM — A 5.2GHz Low Power Transceiver RFIC for WLAN Applications p.5

Y. Shi, F. Dai, J. Yan, X. Hu, Q. Xu, H. Xu, and X. Zhang

(1.3) 10:40 – 11:05 AM — A 4-GHz Band Ultra-Wideband Voltage Controlled Oscillator IC using 0.35 um SiGe BiCMOS Technology p.9

S. Kurachi, Y. Murata, S. Ishikawa, N. Itoh, K. Yonmura, and T. Yoshimasu

(1.4) 11:05 – 11:30 AM — A Direct-Conversion Mixer with a DC-offset Cancellation for WLAN Receiver (Student) p.13

Q. Xu, X. Hu, Y. Jan, Y. Shi, F. Dai, and R. Jaeger

2. Towards TeraHertz Transistors

Monday AM – *Ballroom 2*

Session Chair: J. Prasad

Co-chair: C. Bulucea

(2.1) 9:50 – 10:40 AM — On the Feasibility of Few-THz Bipolar Transistors (Invited) p.17

M. Rodwell, E. Lind, Z. Griggith, S. R. Bank, A. M. Crook, U. Singisetti, M. Wistey, G. Burek, and A. C. Gossard

(2.2) 10:40 – 11:05 AM — On the Frequency Limits of SiGe HBTs for TeraHertz Applications (Student) p.22

J. Yuan, R. Krithivasan, J.D. Cressler, M. Khater, D. Ahlgren, and A. Joseph

(2.3) 11:05 – 11:30 AM — On the Use of Cryogenic Measurements to Investigate the Potential of Si/SiGe:C HBTs for Terahertz Operation p.26

P. Chevalier, N. Zerounian, B. Barbalat, F. Aniel, and A. Chantre

3. SiGe Complementary BiCMOS

Monday AM — *Ballroom 3*

Session Chair: K. Yonemura

Co-Chair: K. Oda

(3.1) 9:50 – 10:15 AM — PNP SiGe:C HBT Optimization in a Low-Cost CBiCMOS Process p.30

D. Knoll, B. Heinemann, Y. Yamamoto, H. E. Wulf, and D. Schmidt

(3.2) 10:15 – 10:40 AM — Development of a Self-Aligned PNP HBT for a Complementary Thin-SOI SiGeC BiCMOS Technology (Student) p.34

J. Duvernay, F. Brossard, G. Borot, L. Boissonnet, B. Vandelle, L. Rubaldo, F. Deleglise, G. Avenier, P. Chevalier, B. Rauber, D. Dutartre, and A. Chantre

(3.3) 10:40 – 11:05 AM — A 10V Complementary SiGe BiCMOS Foundry Process for High-Speed and High-Voltage Analog Applications p.38

T. Tominari, M. Miura, H. Shimamoto, M. Arai, Y. Yoshida, H. Sato, T. Aoki, H. Nanami, S. Wada, H. Hosoe, K. Washio, and T. Hasimoto

(3.4) 11:05 – 11:30 AM — BICOM3HV - A 36V Complementary SiGe Bipolar- and JFET-Technology p.42

W. Schwartz, H. Yasuda, Ph. Steinmann, W. boyd, W. Meinel, D. Hannaman, and S. Parsons

4. Data Converters and Oscillators

Monday PM – *Ballroom 1*

Session Chair: B. Hecht

Co-Chair: J. Haslett

(4.1) 1:30 – 1:55 PM — A 30 GS/s 4-Bit Binary Weighted DAC in SiGe BiCMOS Technology (Student) p.46
S. Halder and H. Gustat

(4.2) 1:55 – 2:20 PM — A 12-bit 65 MS/s Pipeline A/D Converter in 0.18 μm SiGe BiCMOS Technology (Student) p.50

S. Devarajan, R. Gutmann, and K. Rose

(4.3) 2:20 – 2:45 PM — Varactorless, Tuneable LC-VCO for Microwave Frequencies in a 0.25 μm SiGe BiCMOS Technology p.54

H. Veenstra and E. van der Heijden

5. Large-Signal Bipolar Modeling

Monday PM – *Ballroom 2*

Session Chair: L. Nagel

Co-Chair: T. Zimmer

(5.1) 1:30 – 1:55 PM — Large-signal Modeling of High Efficiency SiGe HBTs for Power Amplifier Applications p.58

R. Malladi, M. McPartlin, A. Joseph, H. Lafontaine, and M. Doherty

(5.2) 1:55 – 2:20 PM — Improvement of the Transfer Current Modeling in HICUM/L0 (Student) p.62

C. Thiele, J. Berkner, and W. Klein

(5.3) 2:20 – 2:45 PM — Large Signal RF Characterization of Bipolar Transistors (Invited) p.66

M.N. Tutt and E. Johnson

6. Power Devices

Monday PM — *Ballroom 3*

Session Chair: T. Krustsick

Co-Chair: P. Mawby

(6.1) 1:30 – 2:20 PM — SOI-based Devices and Technologies for High Voltage ICs (Invited) p.74

F. Udrea

(6.2) 2:20 – 2:45 PM — High Speed Junction Diodes in BiCMOS Technologies p.82

S. Pendharkar and J. Trogolo

(6.3) 2:45 – 3:10 PM — New Electrothermal Modeling Tools for Automotive Powers Circuits Design Optimization p.86

W. Habra, P. Tounsi, Ph. Dupuy, J-M. Dorkel, and F. Madrid

7. DBS Tuner and PAs

Monday PM – *Ballroom 1*

Session Chair: D. Lie

Co-Chair: L. Oever

(7.1) 3:30 – 4:20 PM — A BiCMOS SiGe Direct-Conversion DBS Satellite TV Tuner with on-chip ADCs for SiP Integration with a CMOS Demodulator-on-Host (Invited) p.90

A. Maxim

(7.2) 4:20 – 4:45 PM — A Quad-Band GSM/EDGE-Compliant SiGe-Bipolar Power Amplifier with 35.9 dBm / 32.3 dBm Output Power at 56% / 44% PAE p.98

*B. Sogl, W. Bakalski, M. Zannoth, M. Asam, B. Kapfelsperger, J. Berkner, B. Eisner, W. Osterreicher, E. Rampf
A. L. Scholtz, and B. U. Klepser*

(7.3) 4:45 – 5:10 PM — The Doherty Power Amplifier with Collector Current and Voltage Controls for Handset Application p.102
H. Bui, D. Teeter, D. Widay, and S. Mil' shtein

8. Data Transceivers

Monday PM – Ballroom 2

Session Chair: S. Voinigescu

Co-Chair: D. Friedman

(8.1) 3:30 – 4:20 PM — Challenges in Cell-Based Design of Very-High-Speed Si-Bipolar IC's at 100 Gb/s (Invited) p.106
M. Moeller

(8.2) 4:20 – 4:45 PM — A 10 Mbps SiGe BiCMOS Transceiver for Operation Down to Cryogenic Temperatures (Student) p.115
S. Finn, J. Yuan, R. Krithivasan, L. Najafzadeh, P. Cheng, and J. D. Cressler

(8.3) 4:45 – 5:10 PM — 0.155-2.5Gbps SiGe BiCMOS Burst-Mode Laser Driver Using a Digital Implementation of the Automatic Power Control Loop p.119
A. Maxim

9. Thermal Effects, Modeling, and Reliability

Monday PM – Ballroom 3

Session Chair: N. Rinaldi

Co-Chair: J.-S. Rieh

(9.1) 3:30 – 3:55 PM — Modeling of Bandgap Narrowing for Consistent Simulation of SiGe HBTs Across a Wide Temperature Range (Student) p.123
L. Luo, G. Niu, and J.D. Cressler

(9.2) 3:55 – 4:20 PM — Analysis of Electrothermal Effects in Bipolar Current Mirrors p.127
V. d'Alessandro, L. K. Navner, P. J. Zampardi, and N. Rinaldi

(9.3) 4:20 – 4:45 PM — Electrothermal Effects in Bipolar Differential Pairs (Student) p.131
L. La Spina, V. d'Alessandro, F. Santagata, N. Rinaldi, and L. K. Navner

(9.4) 4:45 – 5:10 PM — Large-Signal Performance, Linearity, and Reliability Characteristics of Aggressively-Biased Cascode SiGe HBTs for Power Amplifier Applications (Student) p.135
C. Grens, J.D. Cressler, and A. Joseph

Tuesday, October 2, 2007

10. Emerging Technologies

Tuesday AM – Grand Ballroom

Session Chair: David Ngo

(10.1) 8:30 – 9:10 AM — More Than Moore's Law: Nanofabrics and Architectures (Invited) p.139
K. Wang, A. Khitun, and K. Galatsis

(10.2) 9:10 – 9:50 AM — Ultra-low Voltage Analog Integrated Circuits for Nanoscale CMOS (Invited) p.144
P. Kinget

(10.3) 9:50 – 10:30 AM — High-Voltage Low-Power Analog Design in Nanometer CMOS Technologies (Invited) p.149
S. Bazarjani

(10.4) 10:30 – 11:10 AM — Advanced Packaging: The Redistributed Chip Package (Invited) p.155
B. Keser, C. Amrine, T. Doung, S. Hayes, G. Leal, W. Lytle, D. Mitchell, and R. Wenzel

11. Radar and Wireless Sensors

Tuesday AM – *Ballroom 1*

Session Chair: F. Dai

Co-Chair: P. Davis

(11.1) 11:30 – 11:55 AM — Highly Efficient Class E SiGe Power Amplifier Design for Wireless Sensor Network Applications p.160

D. Lie and J. Lopez

(11.2) 11:55 – 12:20 PM — 17GHz RF Front-Ends for Low-Power Wireless Sensor Networks p.164

W. Wu, M. Sanduleanu, X. Li, and J. R. Long

(11.3) 12:20 – 12:45 PM — On-chip mm-Wave Passives p.168

W. van Noort, C. Detcheverry, A. Rodriguez, and R. Pijper

(11.4) 12:45 – 1:10 PM — A Monolithic 5-Bit SiGe BiCMOS Receiver for X-Band Phased-Array Radar Systems (Student) p.172

J. Comeau, M. Morton, W-M. Kuo, T. Thrivikraman, J. Andrews, C. Grens, J.D. Cressler, J. Papapolymerou, and M. Mitchell

12. Bipolar Modeling and Characterization

Tuesday AM – *Ballroom 2*

Session Chair: D. Weiser

Co-Chair: W. Kraus

(12.1) 11:30 – 11:55 AM — Physics-Based Scalable Modeling of GaAs HBTs p.176

J. Hu, P. J. Zampardi, C. Cismaru, K. Kwok, and Y. Yang

(12.2) 11:55 – 12:20 PM — High Accuracy Temperature Bipolar Modeling for Demanding Bandgap Application p.180

F. Pourchon, H. Beckrich-Ros, C. Raya, C. Faure, B. Gautheron, J. P. Blanc, B. Reynard, and D. Celi

(12.3) 12:20 – 12:45 PM — Distribution of the Collector Resistance of Planar Bipolar Transistors: Impact on Small Signal Characteristics and Compact Modeling p.184

R. van der Toorn, J. Dohmen, and O. Hubert

(12.4) 12:45 – 1:10 PM — New Method for Oxide Capacitance Extraction p.188

C. Raya, T. Schwartzmann, P. Chevalier, F. Pourchon, D. Celi, and T. Zimmer

13. SiGe mmWave and HV technologies

Tuesday AM – *Ballroom 3*

Session Chair: M. Racanelli

Co-Chair: W. VanNoort

(13.1) 11:30 – 12:20 PM — Second Generation 60-GHz Transceiver Chipset Supporting Multiple Modulations at Gb/s data rates (Invited) p.192

S. Reynolds, A. Valdes- Garcia, B. Floyd, B. Gaucher, D. Liu, and N. Hoivik

(13.2) 12:20 – 12:45 AM — A 0.35 μ m SiGe BiCMOS Technology for Power Amplifier Applications p.198

A. Joseph, Q. Liu, W. Hodge, P. Gray, K. Stein, R. Previti-Kelly, P. Lindgren, E. Gebreselasie, B. Voegeli, P. Candra, R. Malladi, P. Wang, and J. Dunn

(13.3) 12:45 – 1:10 AM — Integration of a 5.5V BV_{ceo} SiGe HBT within a 200 GHz SiGe BiCMOS Process Flow p.202

E. Preisler, N. Matine, J. Zheng, P. Hurwitz, and M. Racanelli

14. mmWave Designs

Tuesday PM – **Ballroom 1**

Session Chair: J. B. Begueret

Co-Chair: S. Mattisson

- (14.1) 2:35 – 3:00 PM — A 77 GHz SiGe Mixer Circuit with LO Active Frequency Multiplier for Automotive Radar (Student)** p.206
M. Hartmann, C. Wagner, K. Seamann, H. Jager, and R. Weigel
- (14.2) 3:00 – 3:25 PM — 60GHz LNA and 15GHz VCO Design for use in Broadband Millimeter-Wave WPAN System** p.210
K. To, P. Welch, D. Scheitlin, B. Brown, D. Hammock, M. Tutt, D. Morgan, S. Braithwaite, J. John, J. Kirchgessner, and W. M. Huang
- (14.3) 3:25 – 3:50 PM — Design of a 70 GHz Power Amplifier using a Digital InP HBT Process (Student)** p.214
T. O'Sullivan, M. Le, P. Partyka, R. Milano, P. M. Asbeck
- (14.4) 3:50 – 4:15 PM — A Single-ended 79 GHz Radar Receiver in SiGe Technology** p.218
L. Wang, S. Glisic, J. Borngraeber, and W. Winkler

15. ESD and Reliability

Tuesday PM – **Ballroom 2**

Session Chair: M. Breil

Co-Chair: S. Pendharkar

- (15.1) 2:35 – 3:00 PM — ESD Protection of Fast Transient Pins in Bipolar Processes** p.222
V. Vashchenko, V. Kuznetsov, and P. J. Hopper
- (15.2) 3:00 – 3:25 PM — High Robustness PNP-based Structure for the ESD Protection of High Voltage I/Os in an Advanced Smart Power Technology** p.226
P. Renaud, A. Gendron, M. Bafleur, and N. Nolhier
- (15.3) 3:25 – 3:50 PM — Safe Operating Area from Self-Heating, Impact Ionization, and Hot Carrier Reliability for a SiGe HBT on SOI** p.230
J. Kim, A. Sadovnikov, T. Chen, and J. Babcock
- (15.4) 3:50 – 4:15 PM — Assessing the High-Temperature Capabilities of SiGe HBTs Fabricated on CMOS-Compatible Thin-Film SOI (Student)** p.234
M. Bellini, J. Cressler, and J. Cai

16. Passive Features

Tuesday PM – **Ballroom 3**

Session Chair: R. M. Rassel

Co-Chair: P. Chevalier

- (16.1) 2:35 – 3:00 PM — Electrically Programmable Fuses for Analog and Mixed Signal Applications in Silicon Germanium BiCMOS Technologies** p.238
E. G. Gebreselasie, S. H. Voldman, Z. X. He, D. Coolbaugh, R. M. Rassel, A. Paganini, T. Kirihata, C. G. Cox, S. A. Mongeon, S. A. St. Onge, J. S. Dunn, R. E. Halbach, and J. M. Lukaitis
- (16.2) 3:00 – 3:25 PM — Impact of Layout and Process on RF and Analog Performances of 3D Damascene MIM Capacitors** p.242
S. Cremer, N. Segura, P. Joubin, M. Marin, M. Thomas, C. Richard, S. Boret, D. Benoit, and S. Bruyere
- (16.3) 3:25 – 3:50 PM — Evaluation of SiGeC HBT Varactor using Different Collector Access and Base-Collector Junction Configuration in BiCMOS Technologies** p.246
Y. Morandini, J.-F. Larchanche, and C. Gaquiere